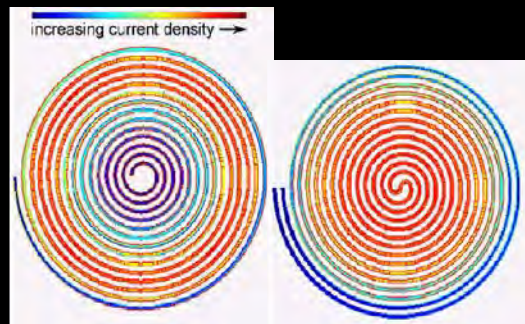
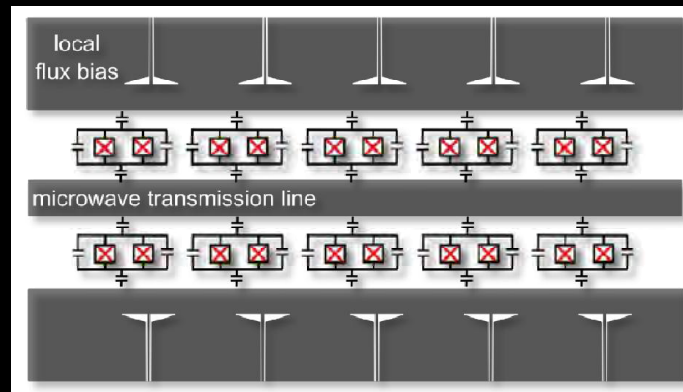
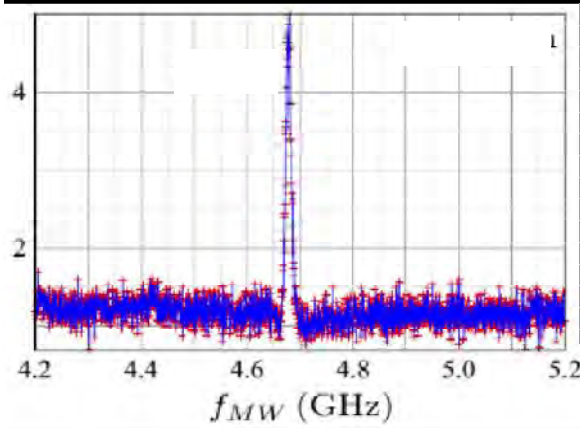


Quantum bits based on superconducting circuits

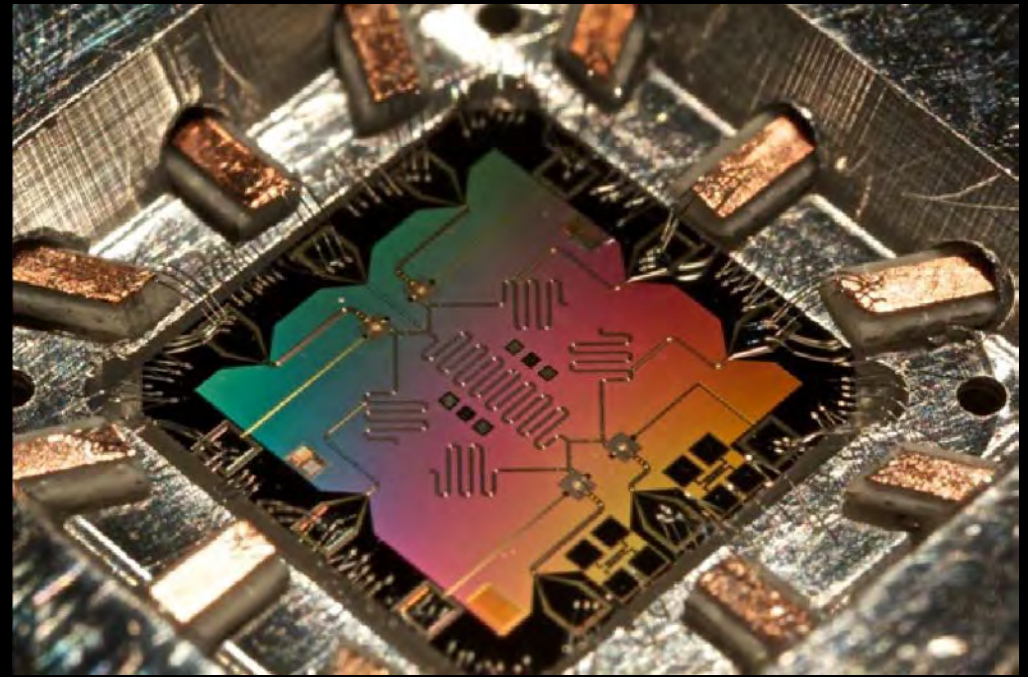
Martin Weides, Karlsruhe Institute of Technology

$$|0\rangle \leftrightarrow |1\rangle$$



Brief history experimental SC qubits

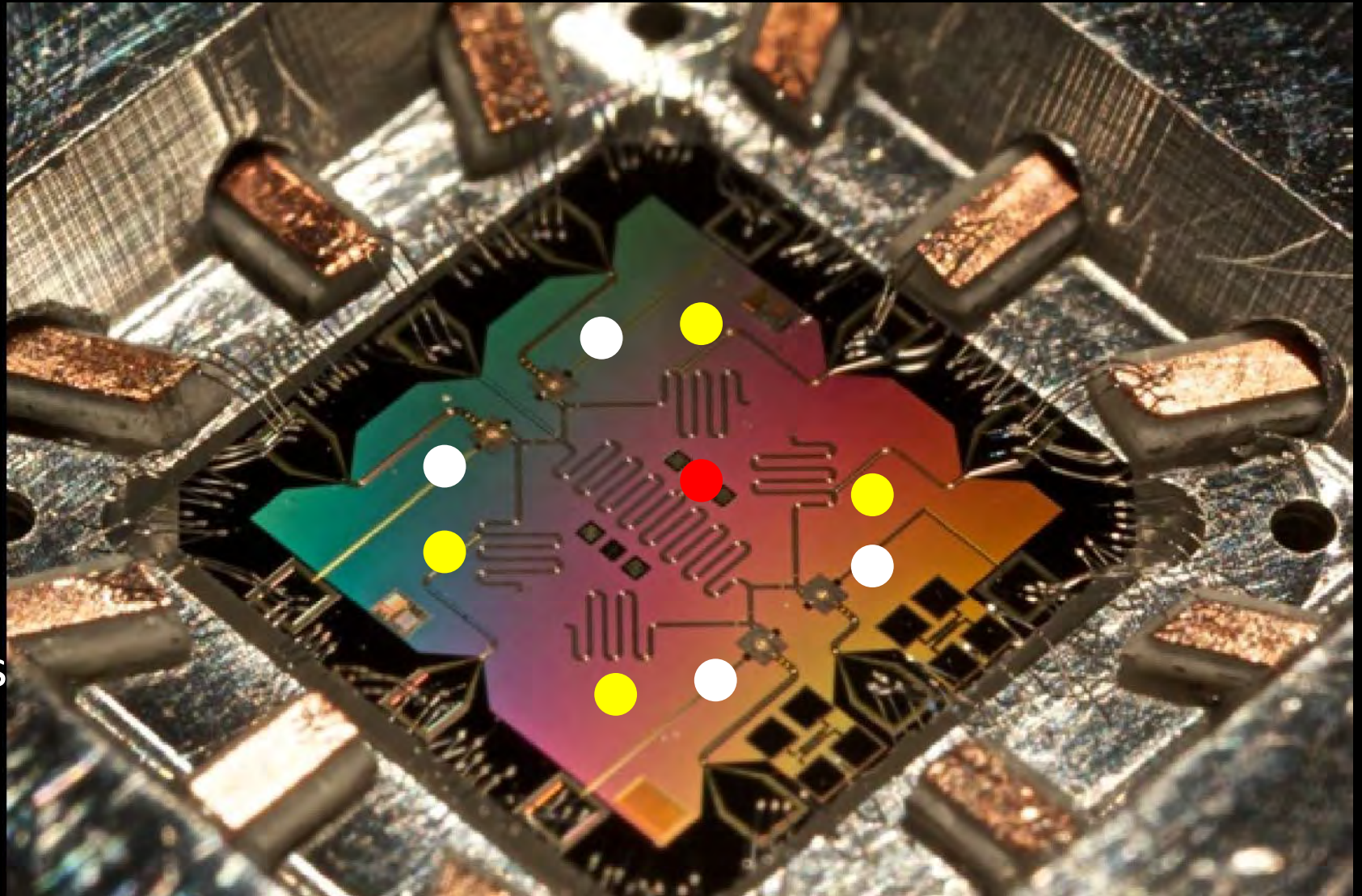
- 1999 Charge (NEC)+flux (Delft) qubits
- 2002 Phase qubit (NIST)
- 2004 cQED with qubits (Yale)
- 2007 Lasering (NEC)
QND (Delft)
- 2008 Fock states (UCSB)
- 2009 Grover and Deutsch–Jozsa (Yale)
Arbitrary quantum states (UCSB)
Bell inequality (UCSB)
- 2010 3-qubit entanglement
(UCSB & Yale)
- 2011 Quantum von Neumann
architecture (UCSB)
- 2012 4 qubits and
5 resonators (UCSB)**
Shor, '15=5x3'



Microstructured quantum processor

(University of California, Santa Barbara)

- Qubit
- Memory
- Signalbus



5 mm

Basic potentials

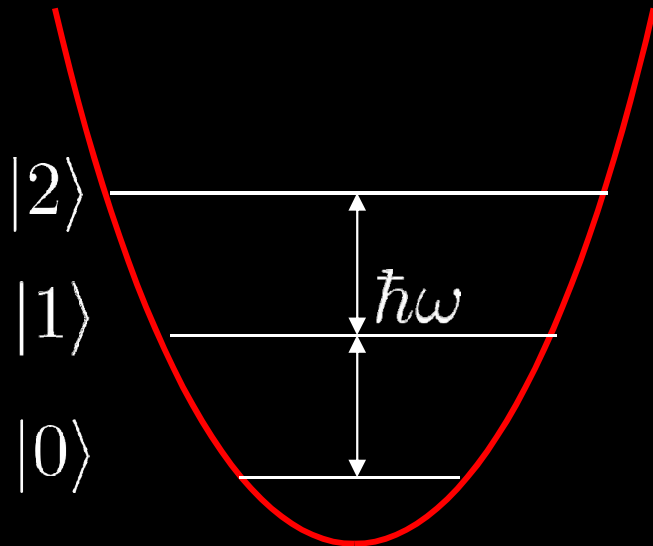
Harmonic oscillator

Photons in cavity, atom oscillation

Energy levels equidistant

Energy eigenstate $|n\rangle$

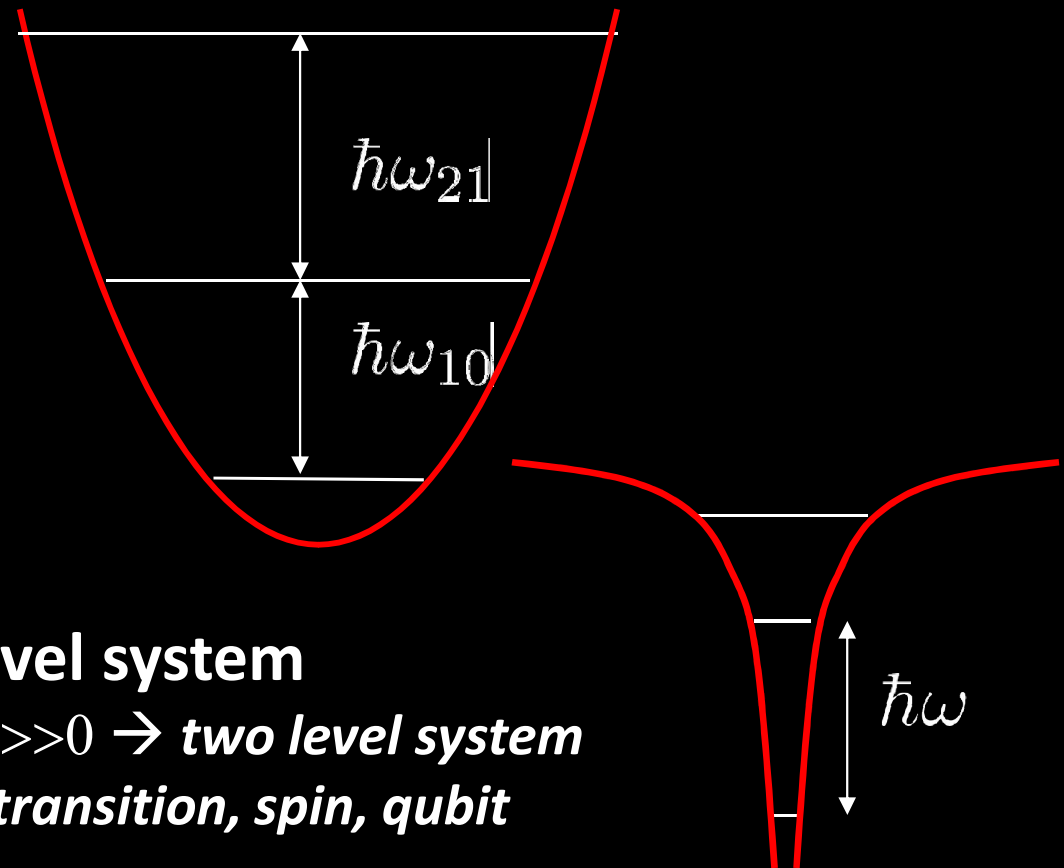
$$\hat{H}_{\text{cavity}} = \left(a^\dagger a + \frac{1}{2}\right) \hbar\omega$$



Anharmonic oscillator

Large excitation amplitudes

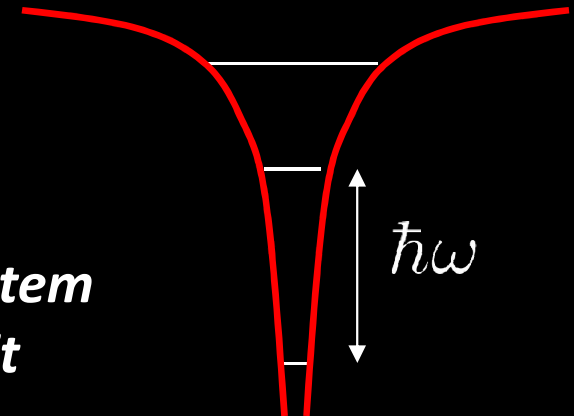
$$\Delta = \omega_{n+1,n} - \omega_{n,n-1}$$



Two level system

if $|\Delta/\omega| \gg 0 \rightarrow$ *two level system*
atomic transition, spin, qubit

$$\hat{H}_{\text{TLS}} = \hbar\omega \frac{\hat{\sigma}_z}{2}$$



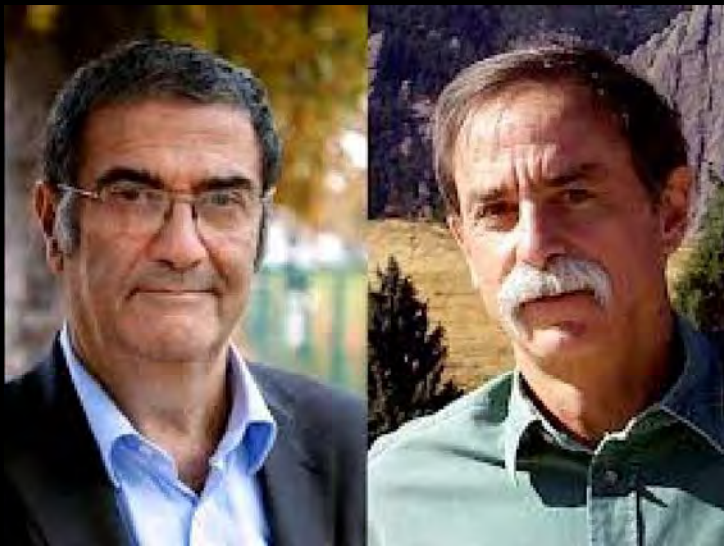
Nobel price 2012



Nobel Prize in Physics 2012 was awarded jointly to

Serge Haroche and David J. Wineland

"for ground-breaking experimental methods that enable measuring and manipulation of individual quantum systems"



Controlling a quantum particle
(atoms or ions)

$$\hat{H} = \hbar\omega_c \hat{a}^\dagger \hat{a} + \hbar\omega_a \frac{\hat{\sigma}_z}{2} + \frac{\hbar\Omega}{2} \hat{E} \hat{S}$$

Jaynes–Cummings
Cavity-qubit system

Quantum information processing, Q-simulation, collective Q-phenomena

Artificial atoms for quantum matter require

Large interaction strength

→ *dipole moment*

Tunability

→ *tune transition frequency*

Frequency selection

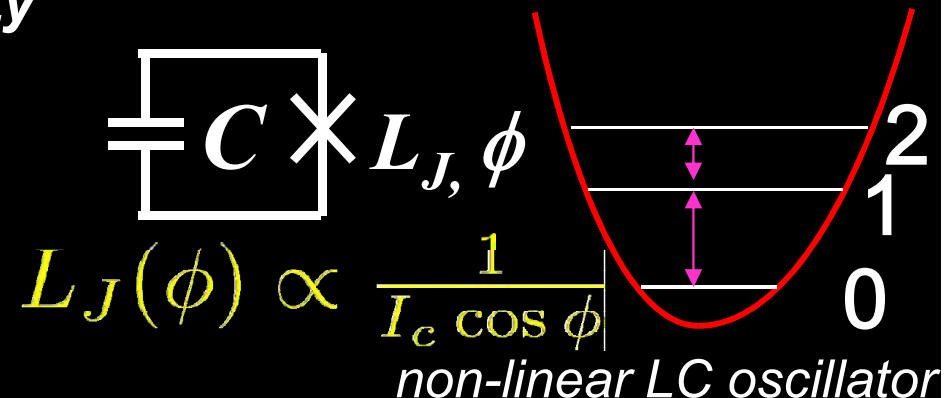
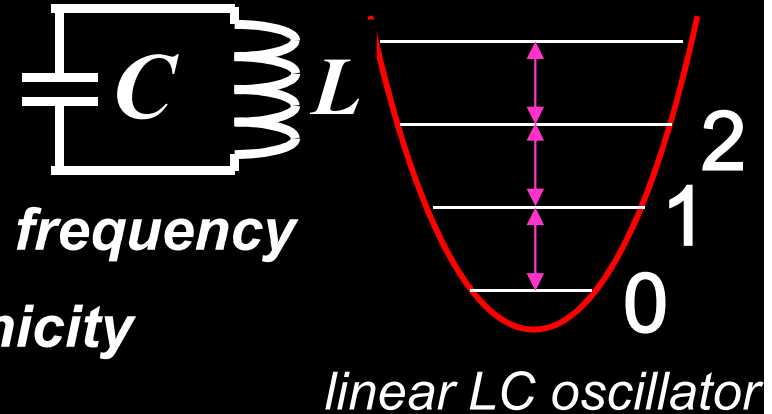
→ *large anharmonicity*

Long coherence

→ *low loss*

High integration density

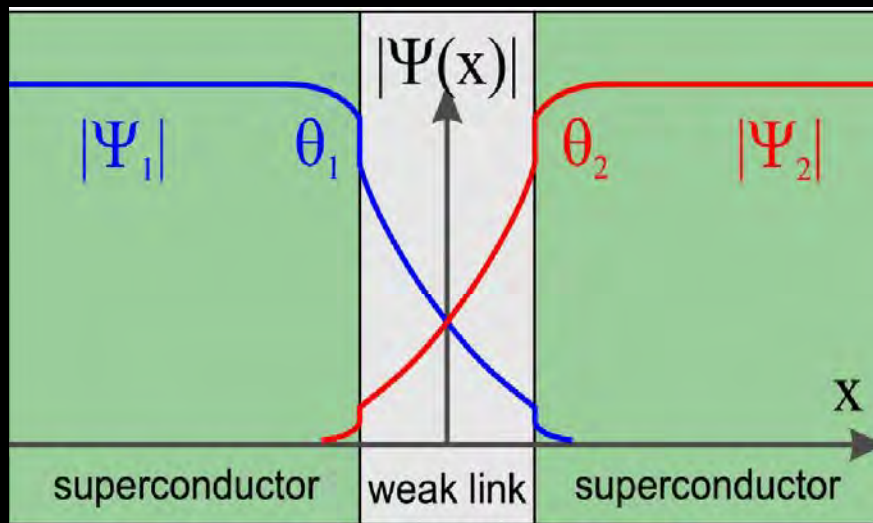
→ *scalability*



Superconducting quantum circuit

- Strong coupling w/ EM field, long coherence, fast & local detuning
- simple resonant circuit design, straightforward scalability
- high density, integration w/ std. electronics

Josephson junction \rightarrow non-linear inductor



$$\Psi = |\Psi| \exp(i\theta)$$

Phase difference

$$\phi = \theta_1 - \theta_2$$

1st Josephson eq.: $I_J = I_c \sin \phi$ (DC)

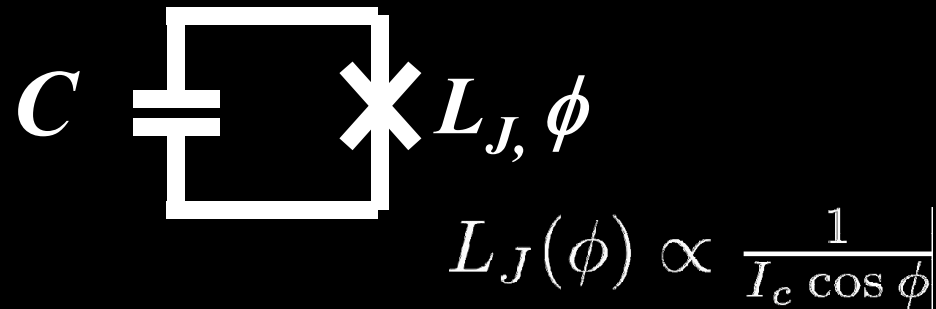
2nd Josephson eq.: $V = \frac{\Phi_0}{2\pi} \frac{\partial \phi}{\partial t}$ (AC)

From DC: $\frac{\partial I_J}{\partial \phi} = I_c \cos \phi$

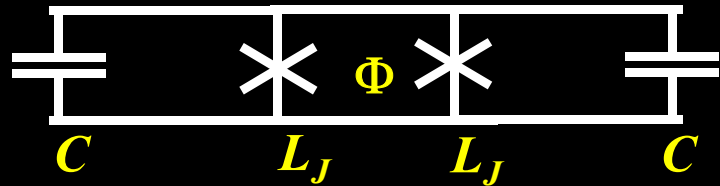
Insert in AC: $V = \frac{\Phi_0}{2\pi} \frac{1}{I_c \cos \phi} \frac{\partial I_J}{\partial t} = L_J \frac{\partial I_J}{\partial t}$

\rightarrow non-linear inductance: $L_J(\phi) = \frac{\Phi_0}{2\pi} \frac{1}{I_c \cos \phi}$

Capacitively shunted Josephson junction → Anharmonic oscillator

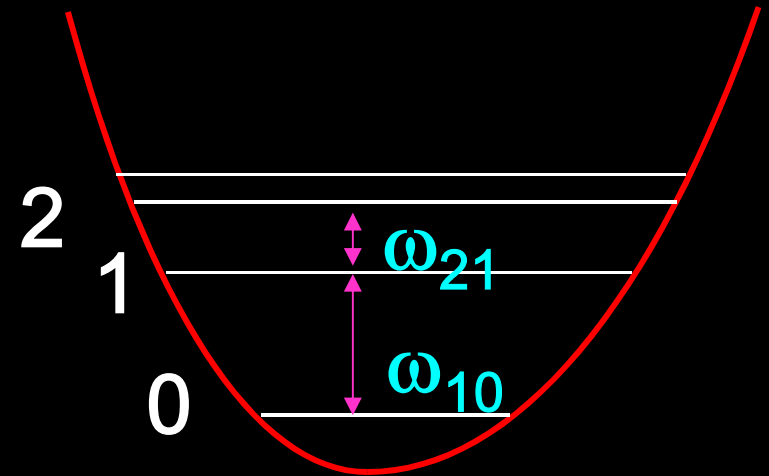


non-linear LC oscillator

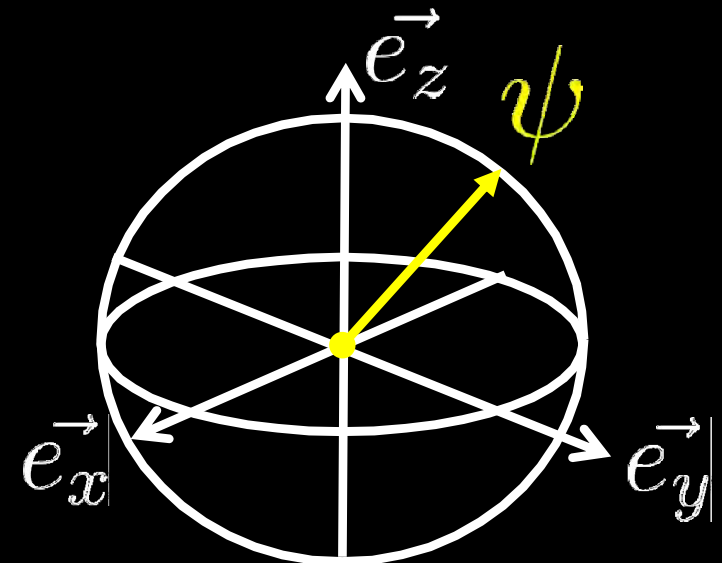


Magnetic flux Φ changes $L_J(\phi)$

$$\omega_{10} = 1/\sqrt{CL_J(\Phi)}$$

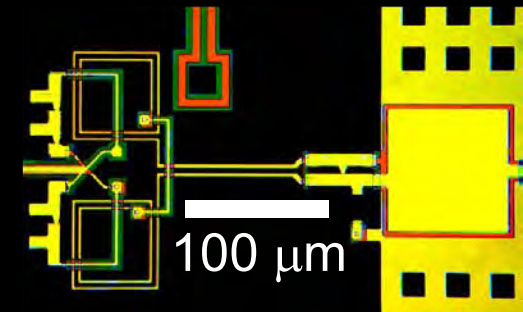
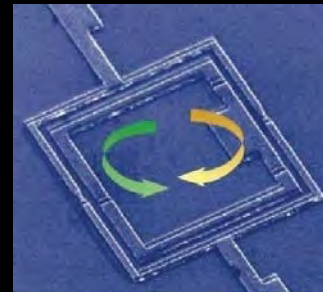
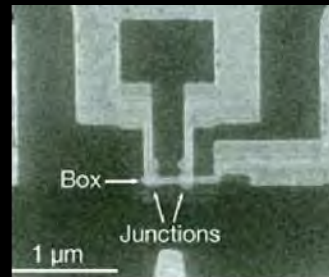


Restrict to two lowest states → **Bloch sphere**



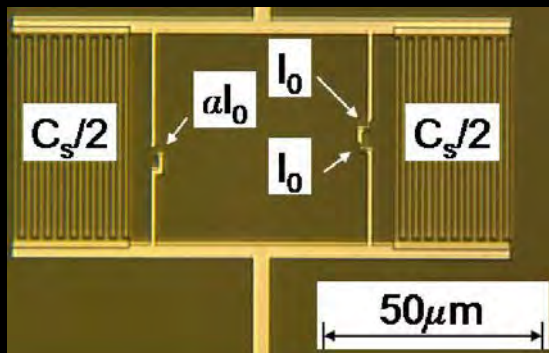
Superconducting qubit 'zoo'

$[\hat{q}, \hat{\phi}] = i\hbar$	<u>Charge</u>	<u>Flux</u>	<u>Phase</u>
$E_J/E_C = \frac{I_c \Phi_0}{2\pi} / \frac{e^2}{2C}$	1	10^2	10^4
Junction area (μm^2)	0.01	0.1-1	1-100

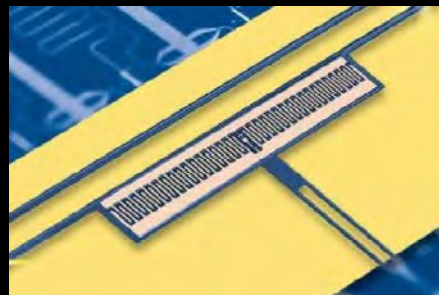


Modern designs

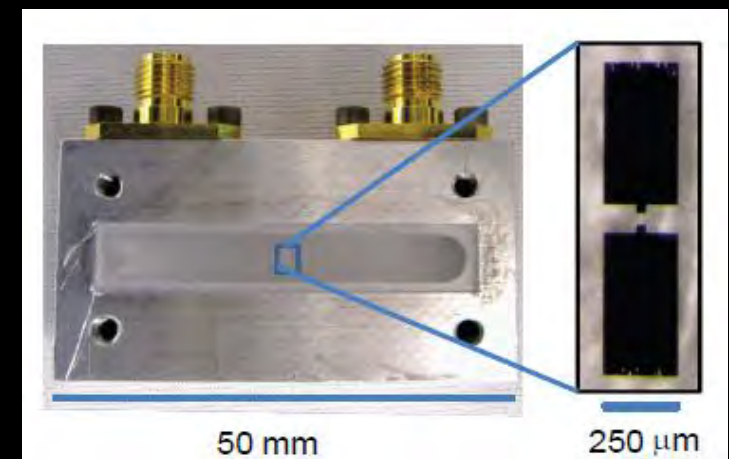
C-shunted flux qubit



Transmon =
C-shunted charge qubit



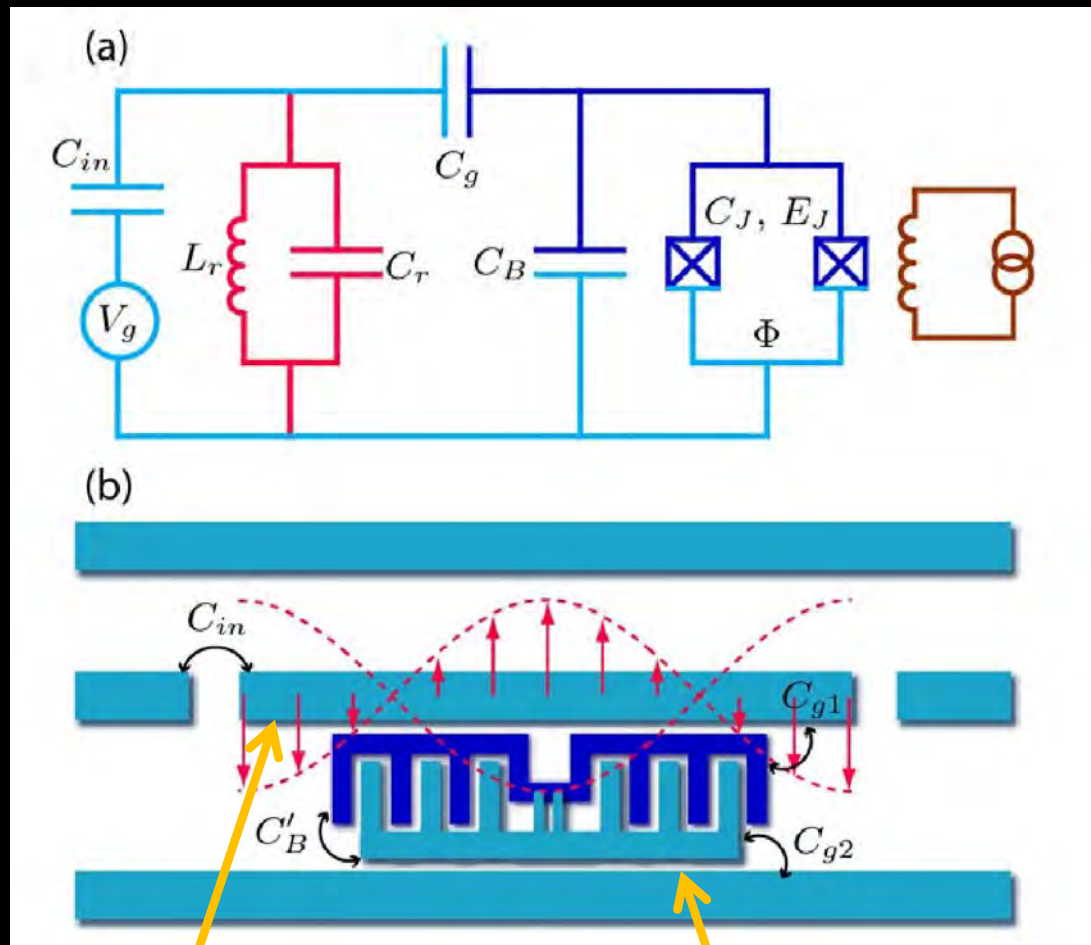
3d transmon



circuit quantum electrodynamics (cQED): artificial atom (qubit) coupled to resonator

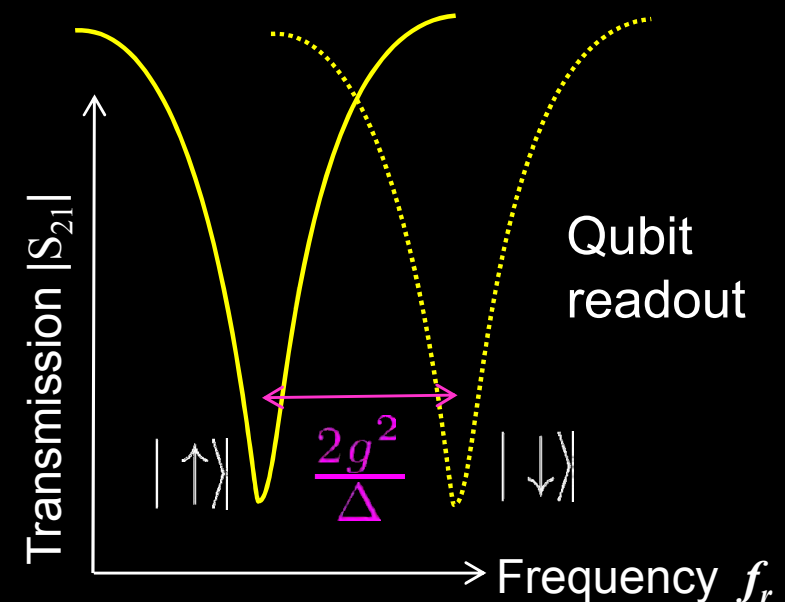
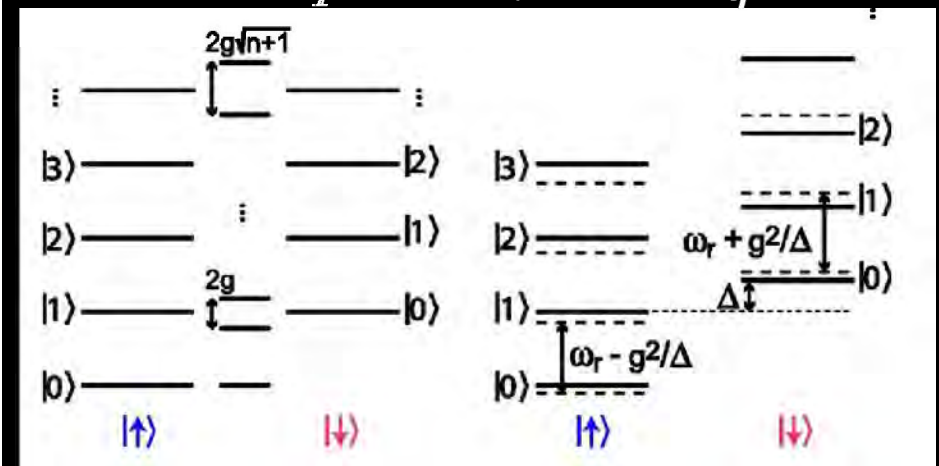
$$\hat{H} = \hbar\omega_r \hat{a}^\dagger \hat{a} + \hbar\omega_q \frac{\hat{\sigma}_z}{2} + \frac{\hbar\Omega}{2} \hat{E} \hat{S} \quad \text{Strong coupling regime possible}$$

$$\omega_r = \omega_q \quad \omega_r = \omega_q - \Delta$$

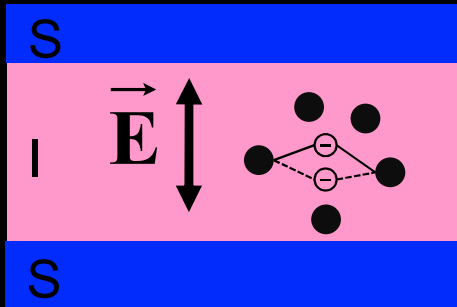


Resonator

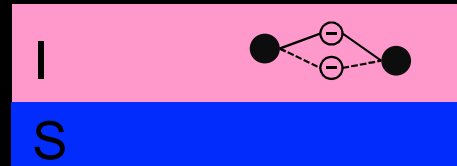
Qubit



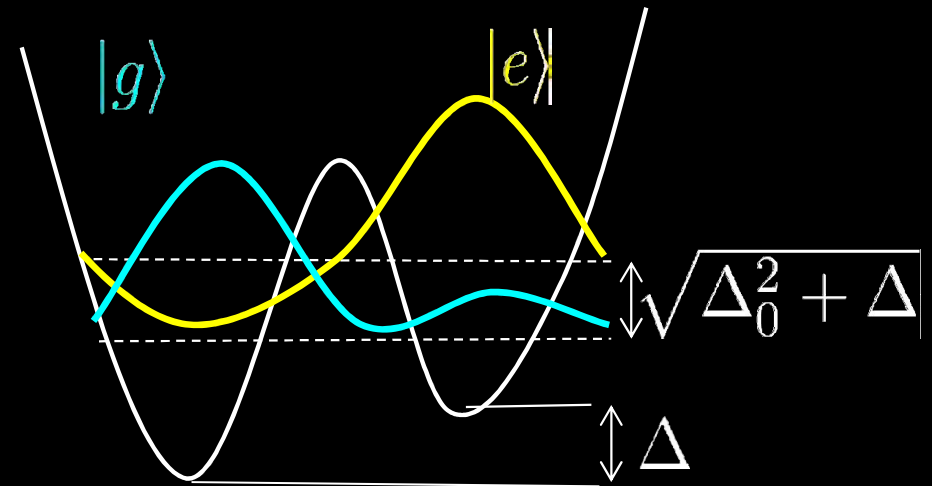
Parasitic two level systems (TLS) in dielectrics



Josephson tunnel junction



resonator



Amorphous oxides loaded with uncompensated charges $\sim 10^{16}/\text{cm}^3$

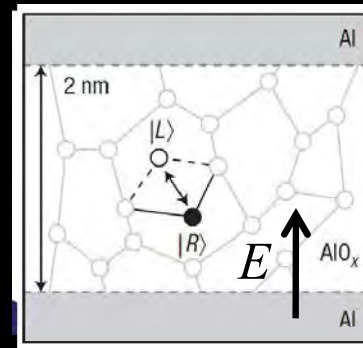
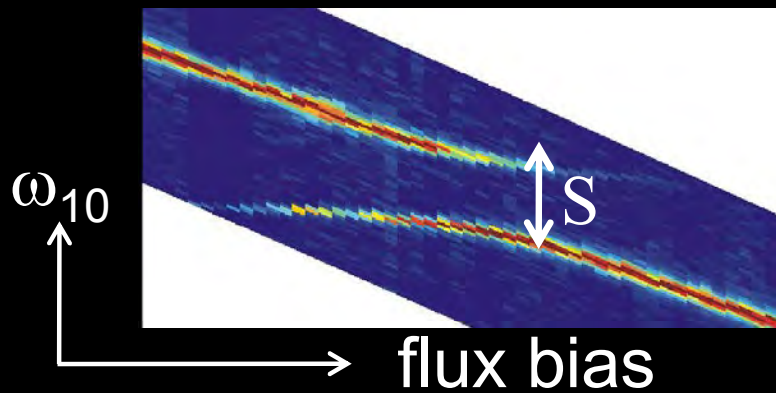
Range of energies, coherence and Rabi frequencies Δ , T_1 , T_2 , Ω

Absorption probability goes as $\sim \frac{\tanh\left(\frac{\hbar\omega}{2k_B T}\right)}{\sqrt{1 + \left(\frac{E}{E_c}\right)^2}}$

Maximized at low E , T

→ Dominating loss at low T & E

Decoherence due to TLS



interaction S lifts degeneracy

Qubit spectroscopy and time domain
TLS located in *tunnel barrier oxide*

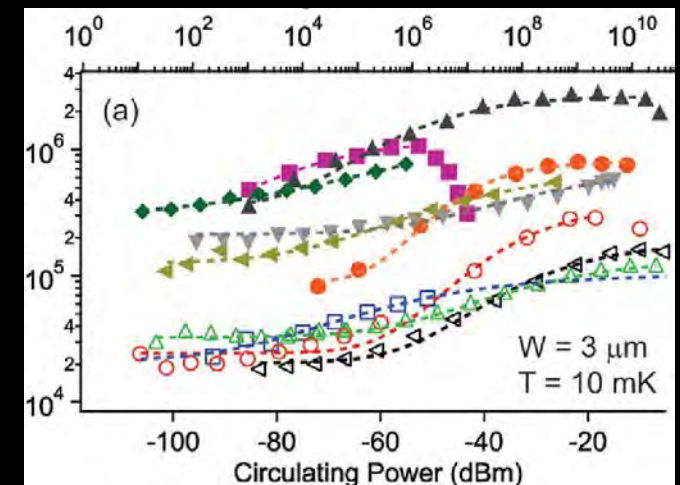
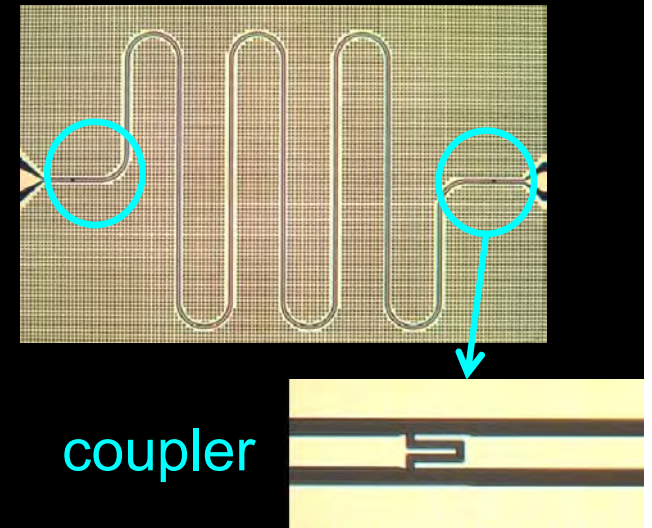
Resonator quality factor
power dependence (TLS saturation)

$$Q^{-1} = Q_{\text{TLS}}^{-1}(E) + Q_{\text{P.I.}}^{-1}$$

$$Q_{\text{TLS}}^{-1} \propto \frac{\tanh\left(\frac{\hbar\omega}{2k_B T}\right)}{\sqrt{1 + \left(\frac{E}{E_c}\right)^2}}$$

Sage *et al.*
JAP '10

$$Q = 1/\tan\delta$$



Coherence threshold quantum error correction

Min. requirement: 0.1‰ error per gate (10 nsec) → 100 μsec

Relaxation T_1 $|1\rangle \rightarrow |0\rangle$

Limited by: *Capacitive and inductive loss, quasiparticles, environmental coupling, microscopic defect states (TLS)*

Dephasing T_2^*, T_2 $|\psi\rangle \rightarrow |\psi\rangle e^{i\phi}$

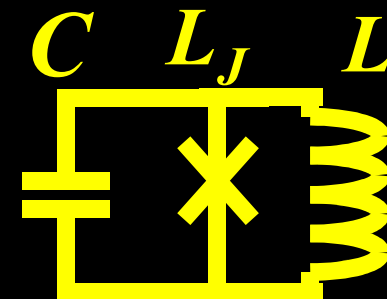
$T_2 \approx 2T_1$ (@ sweet spot), usually shorter

Limited by: *1/f noise (charge, flux)*

$$\frac{1}{T_2} = \frac{1}{2T_1} + \frac{1}{\tau_\phi}$$

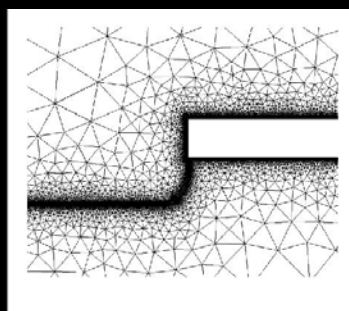
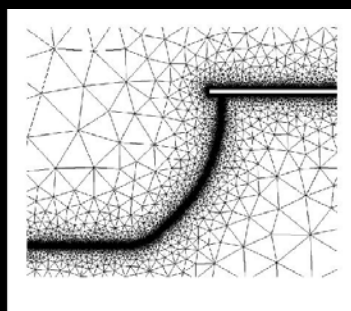
Materials limited:

→ *Junctions, inductors, capacitors*



Field distribution, filling factor of stored energy

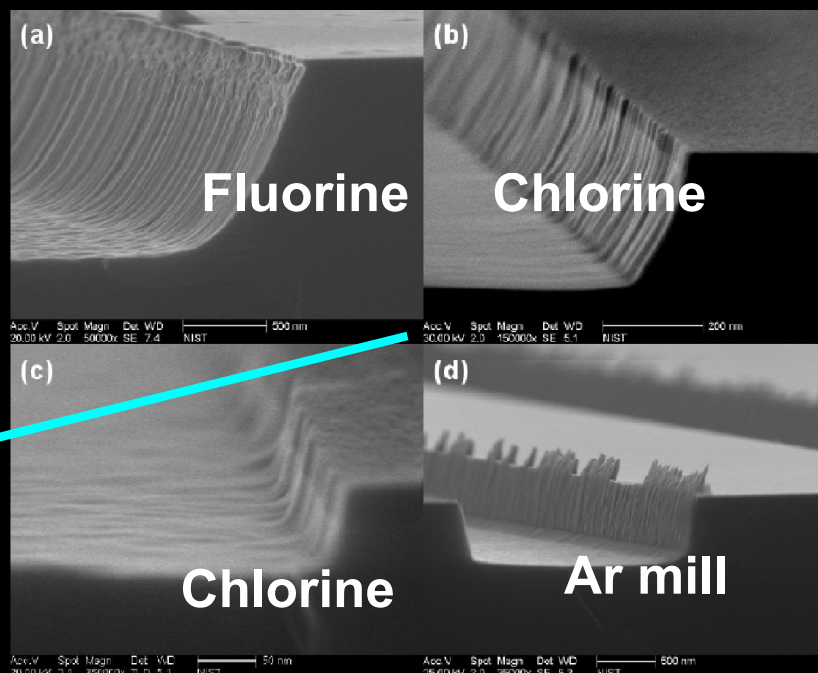
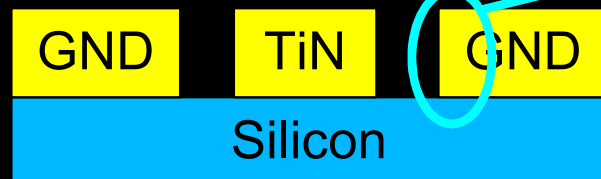
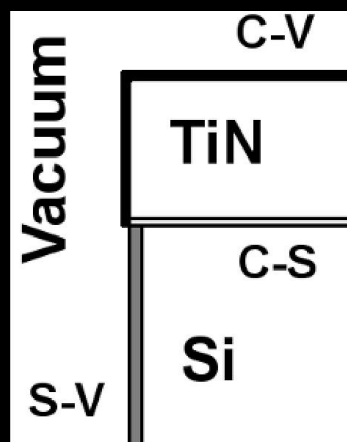
- Etched surface matters, microscopic structure, E-field
- Implications for resonant quantum circuits



vacuum
conductor
substrate

Filling factor:

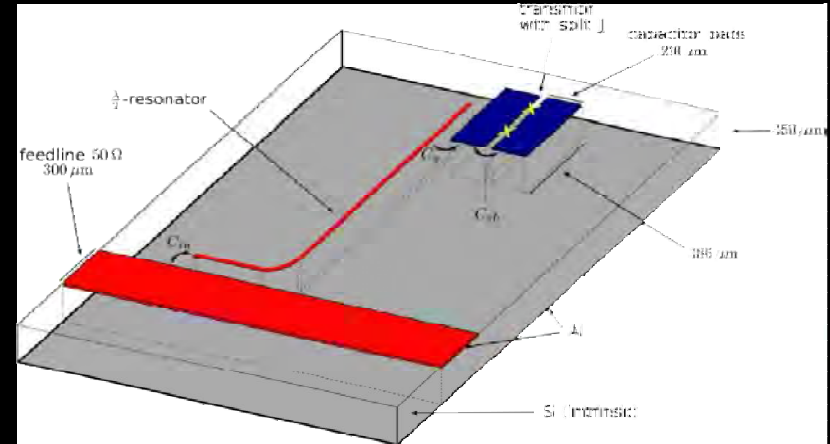
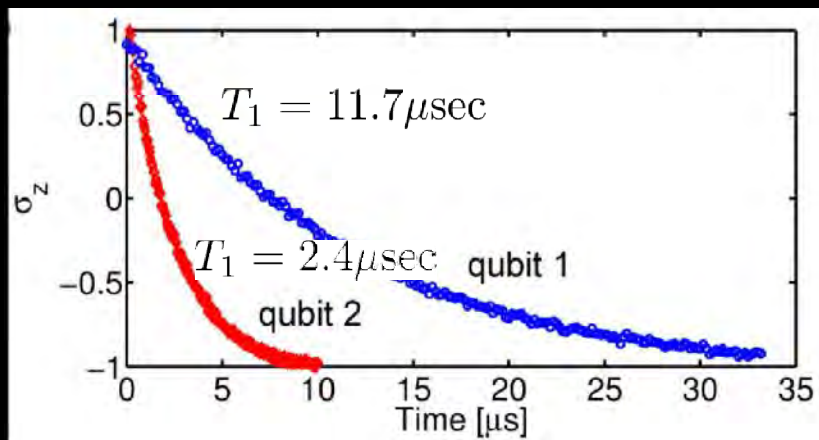
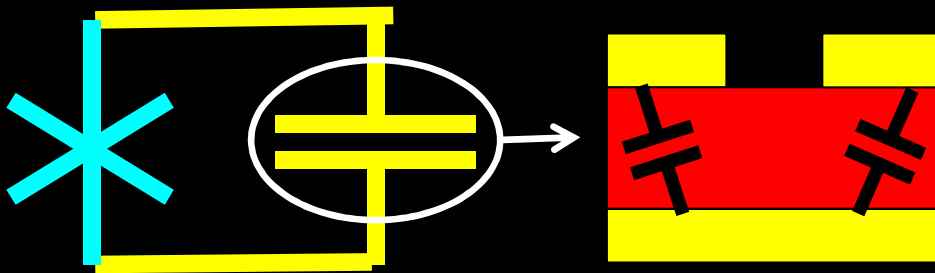
$$F_V = \frac{\int_V \epsilon_V |E(r)|^2 dv}{\int_{V_{\text{tot}}} \epsilon(r) |E(r)|^2 dv}$$



Sandberg *et al.*
APL 2012

Microstrip transmon qubit

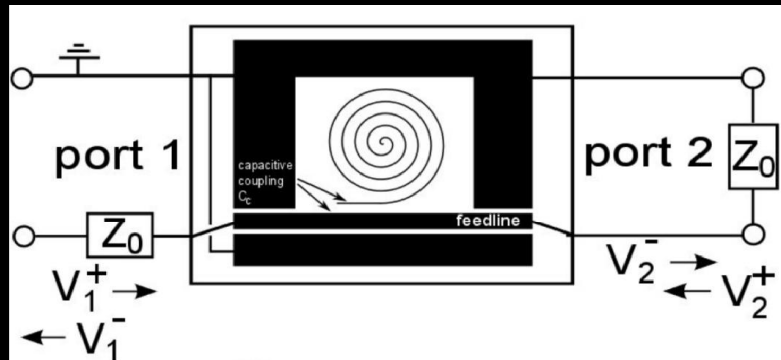
1. Best Josephson junction (T_1) \rightarrow Sub-micron Al-AlO_x-Al
 2. Best capacitor (δ) \rightarrow TiN microstrip w/ low loss silicon substrate
 3. Negligible Al/TiN interface loss \rightarrow Merge sub-micron junctions and TiN capacitor
- Loss participation analysis: \rightarrow expected lifetime dominated by TiN



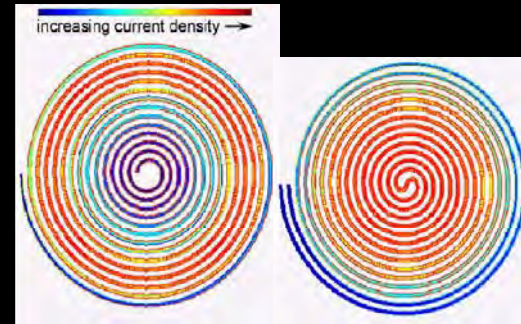
- qubit 1: Purcell limit 20 μ sec
Radiation limit 17 μ sec
Combined limit 9.7 μ sec
- qubit 2: Purcell limited
Re-designed qubit $T_1=40$ μ sec
expect >100 μ sec (error correction threshold)

Engineered quantum elements

Resonator design and simulation

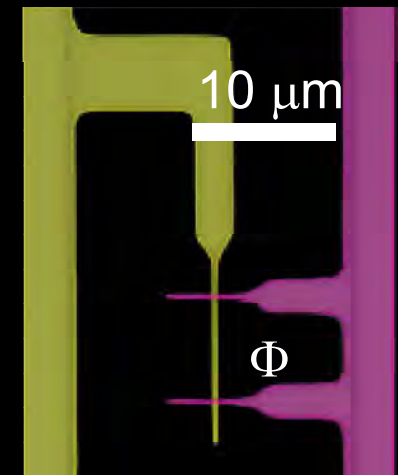


Current distribution

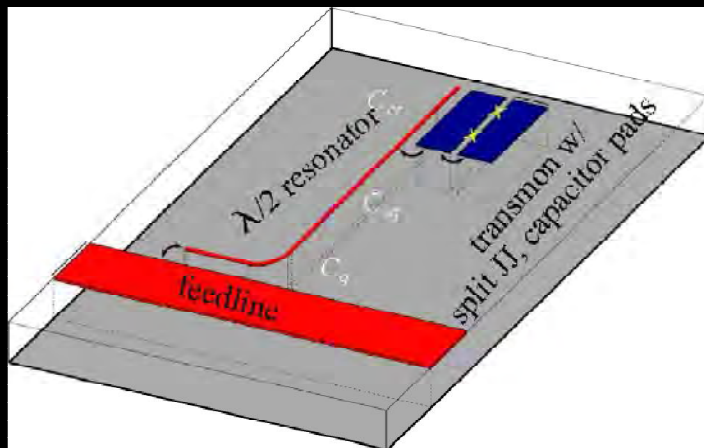


Kiselev, BA thesis '13

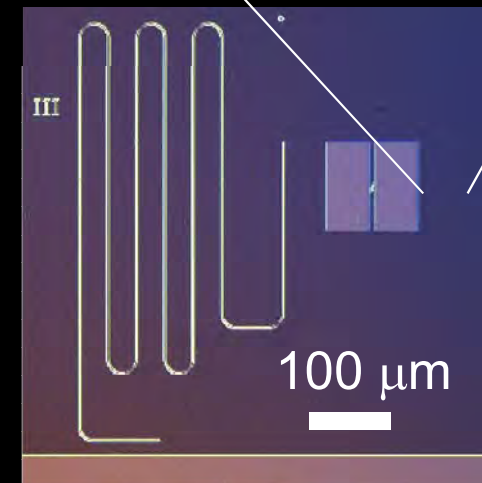
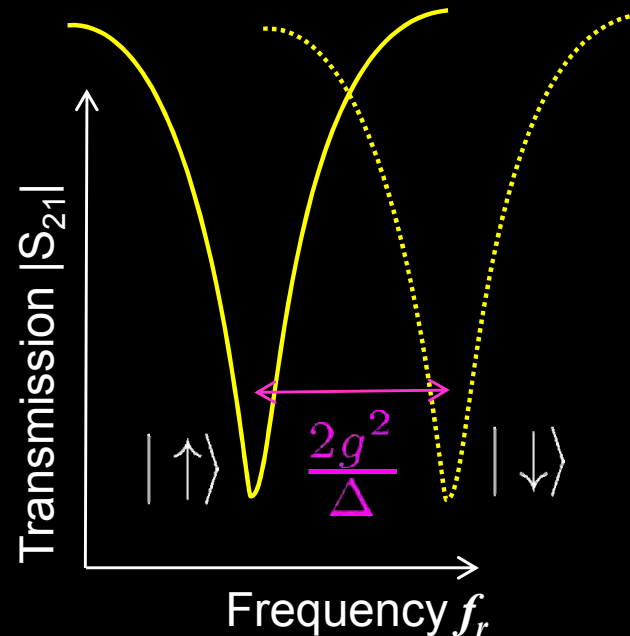
Flux tunable junction



Qubit (Transmon) coupled to resonator



Braumüller, MA thesis '13



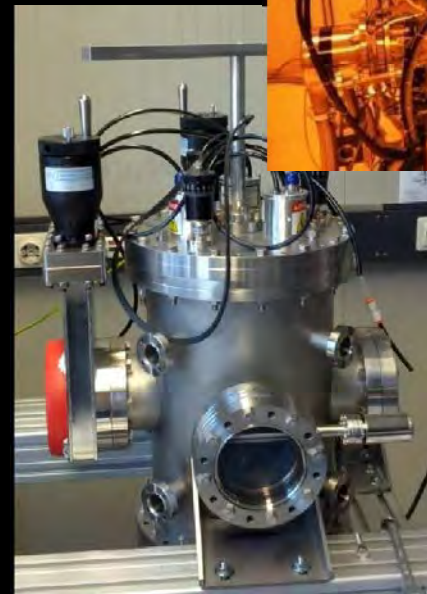
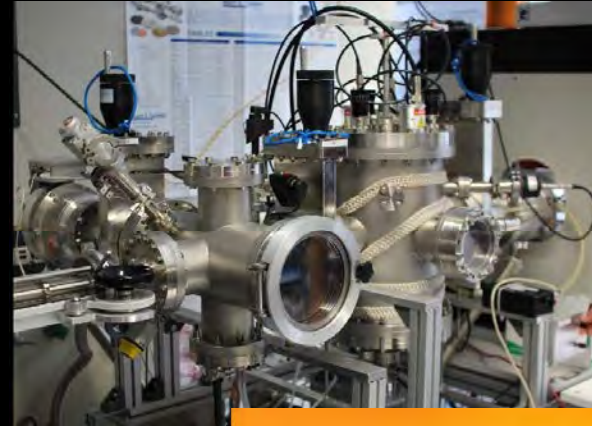
Deposition tools

Fast turnaround, flexibility, reliability, good control

Deposition, cleaning, oxidation

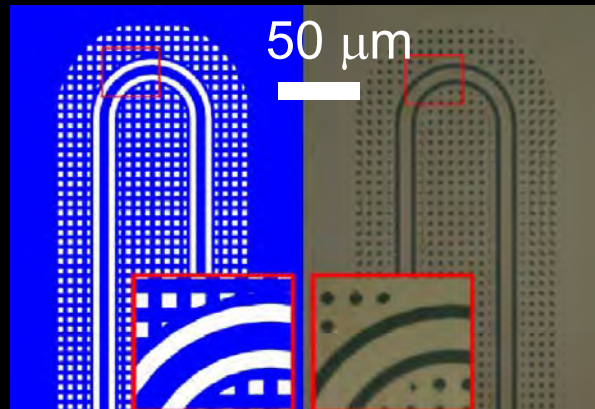
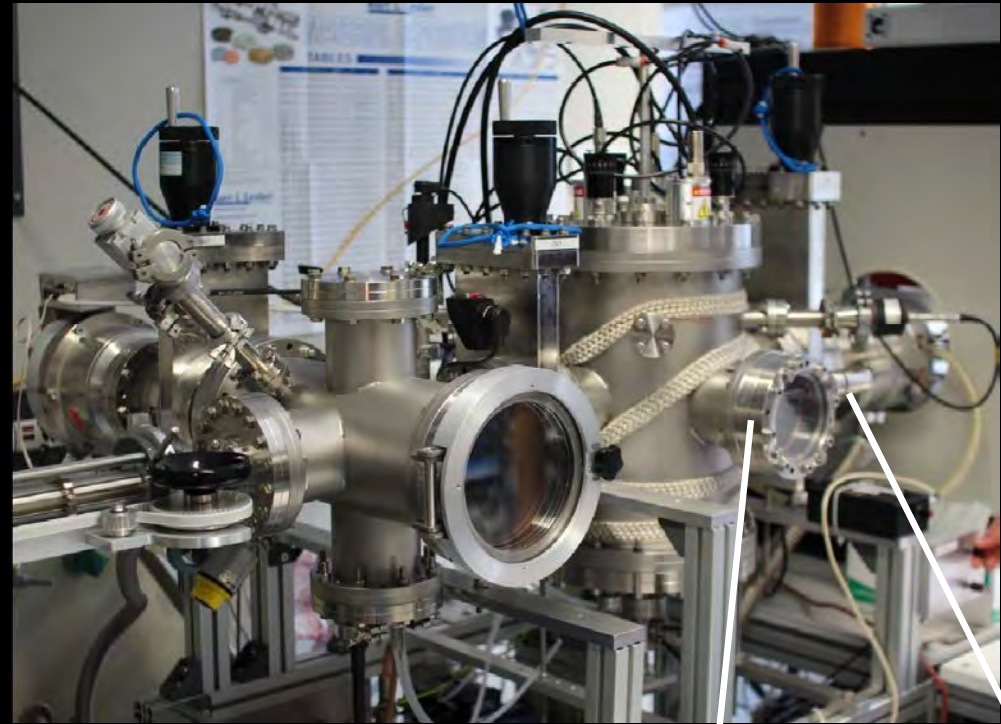
Al-AlO_x-Al tunnel junctions

- **Sputter tool Plasma 1**
 - Al, Nb, NbN, AlO_x resonators
- **Shadow evaporation tool Plassys**
 - E-beam evaporator
 - Al-shadow evaporated junctions
 - Ti/Au markers, AuPd resistors
- **Sputter tool Plasma 2**
 - Nitride superconductors
 - Heating stage (500°C)

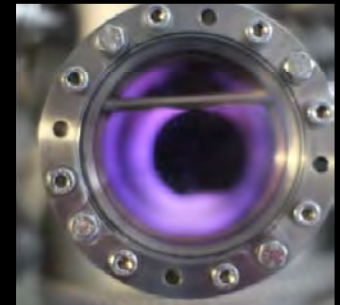
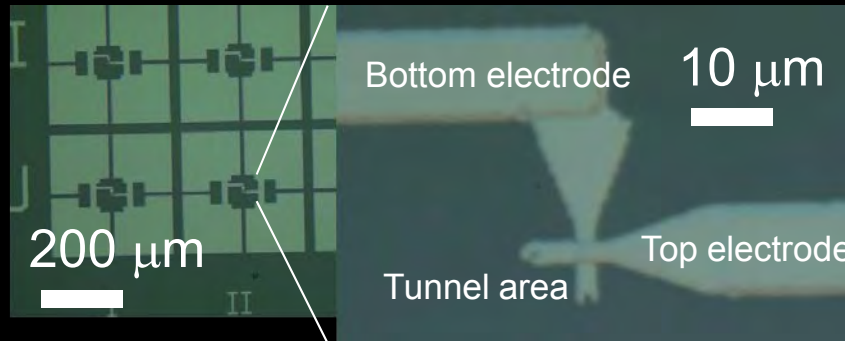


Sputtered thin films

- Fast turnaround, flexibility, reliability, good control
- Deposition
- Cleaning
- Oxidation
- Al, Nb, NbN, AlO_x resonators
- Al- AlO_x -Al tunnel junctions
- Toolbox of designs and materials

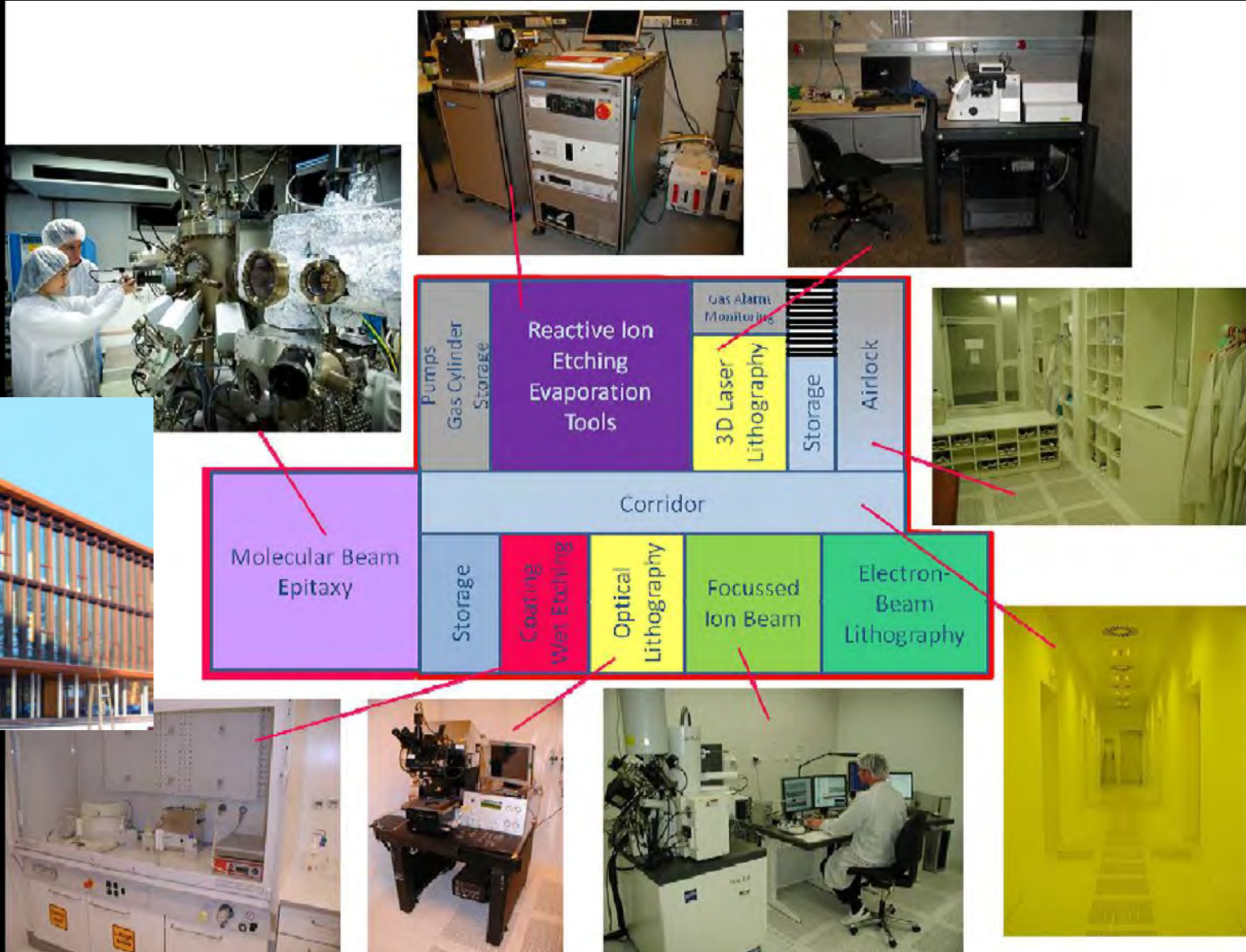


Neuwirth, BA thesis '13



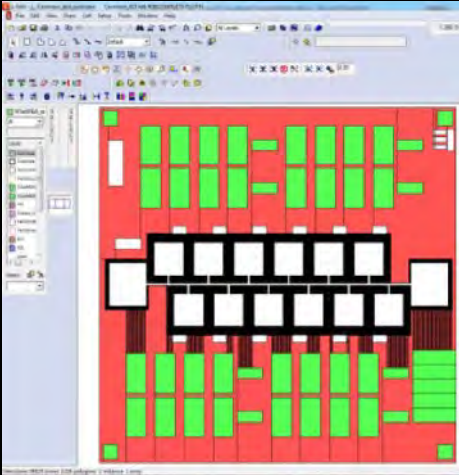
DFG Center for Functional Nanostructures

Nanostructure Service Laboratory

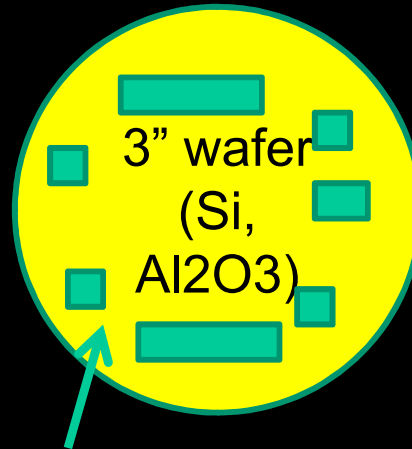


Schematic fabrication

1. Design software

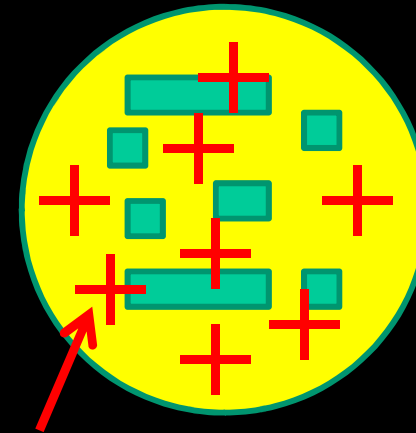


2. Film deposition, optical litho, etch



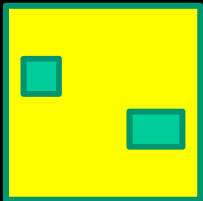
Inductor, capacitor, flux bias...
(1 $\mu\text{m}+$ feature sizes)

3. E-beam markers optical litho



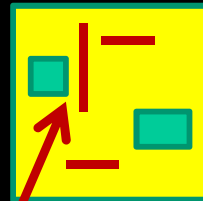
Markers (crosses etc.)

4. Dice into 20x20 mm²



Get 6 chips w/
same designs

5. E-beam litho, Al-AlO_x-Al shadow evaporation



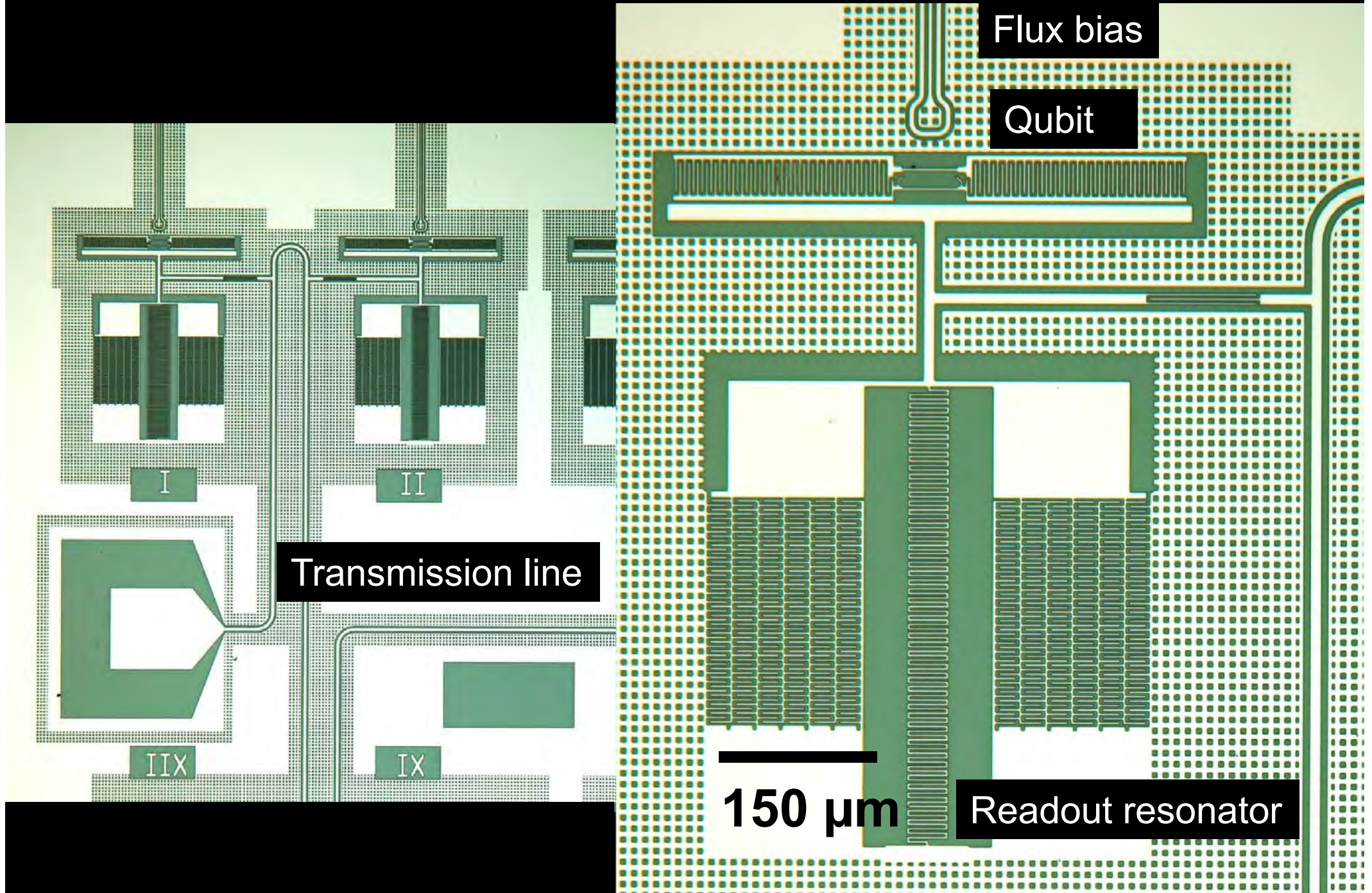
'Dolan' bridges,
Tunnel junctions, ...

6. Dice into 5x5mm²



Get 9 chips w/
different designs

12 qubit chip 'cavemon'



$^3\text{He}/^4\text{He}$ dilution refrigerator

400 mm cold plate

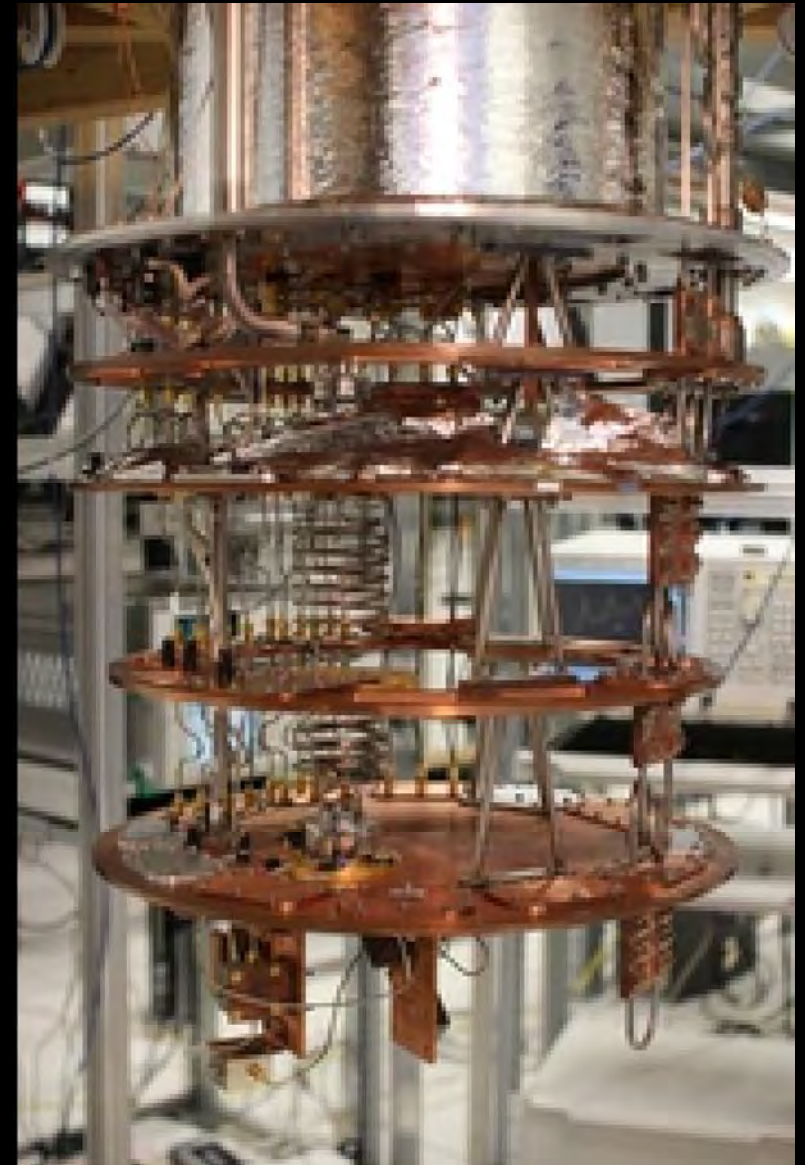
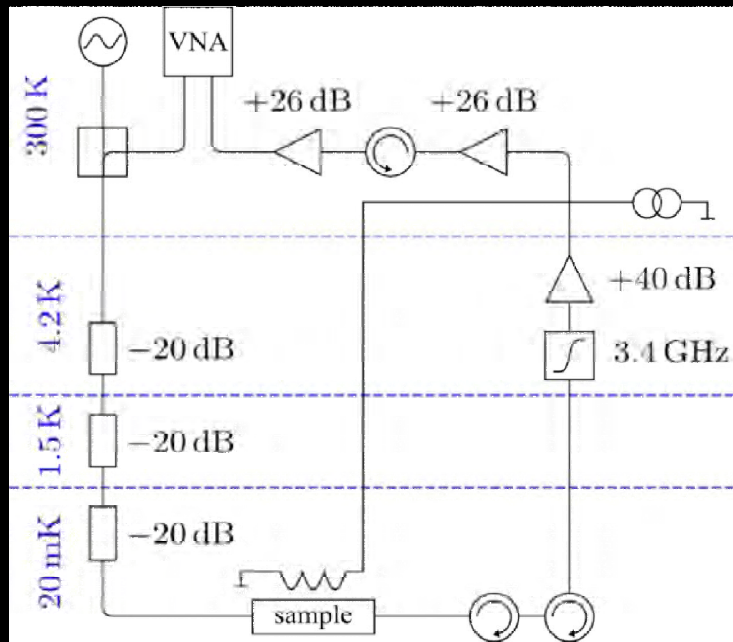
18 coax lines, 24 filtered DC lines

6 HEMTs (2x LNF)

2-port, 4-port microwave switches,
circulators, filters, infrared shield...

Fits 9 samples

Multi-tone spectroscopy, flux bias,
time domain measurements



Materials for quantum circuits

- specific properties for capacitive and inductive regions -

Superconductors

Aluminium

Niobium

Niobium nitride

Aluminium oxide



Josephson junctions

Cross junctions (optical & e-beam, sputtered)

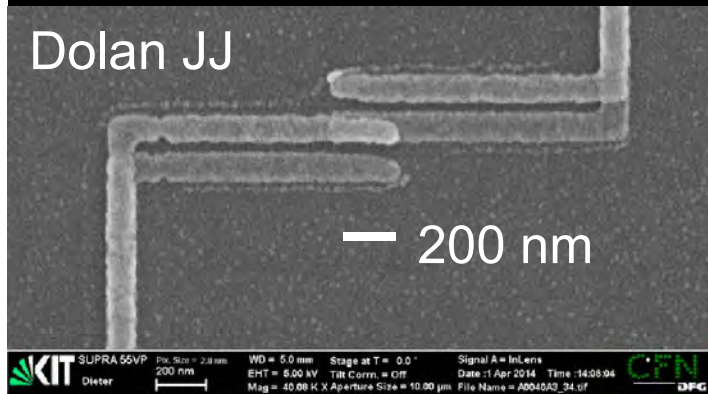
Shadow junctions (e-beam, evaporated)

Josephson tunnel junctions

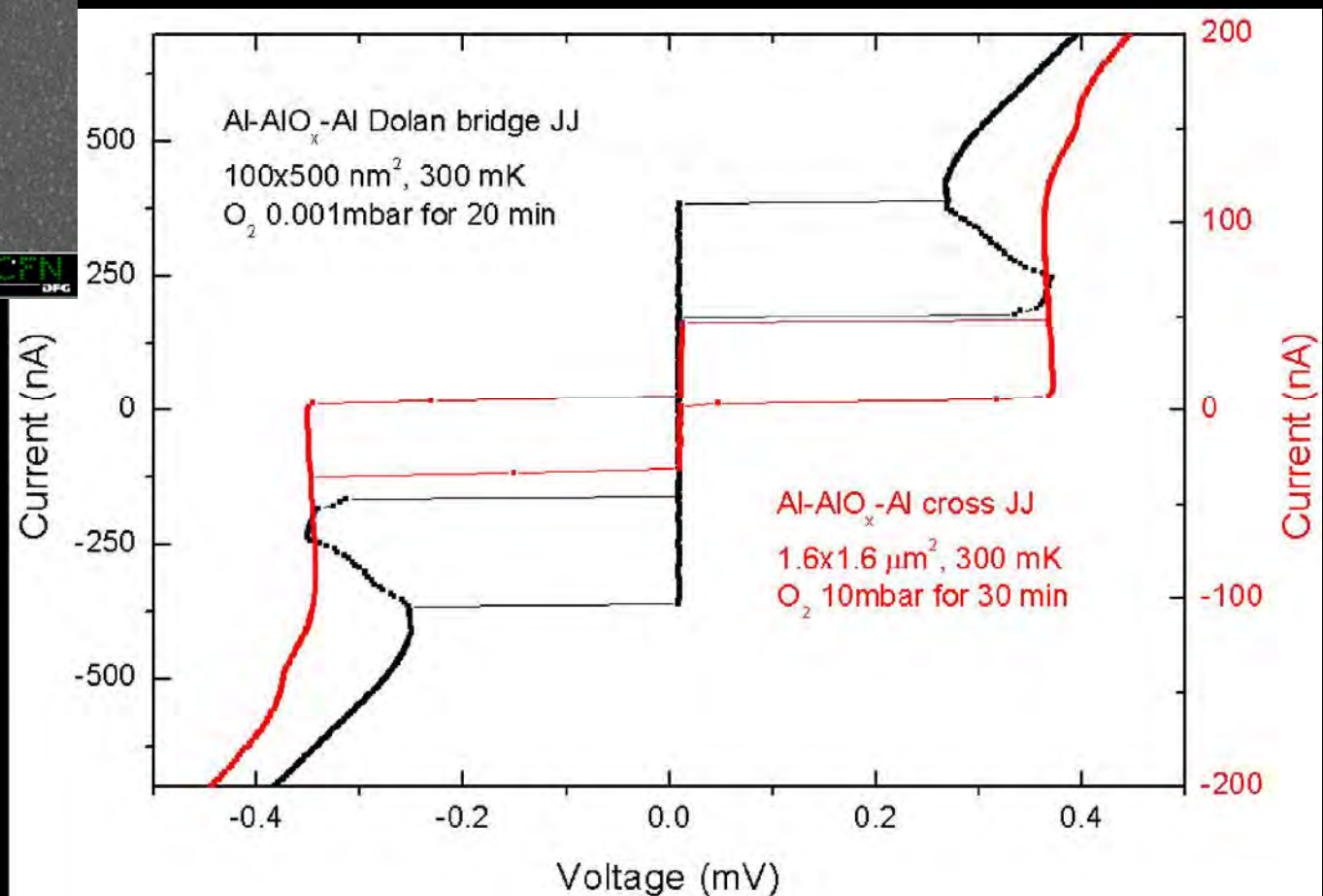
Al-AlO_x-Al junctions

- Ultra-small shadow evaporated (aka *Dolan* JJs)
- Micron-sized *cross* JJs, evaporated and sputtered

Dolan JJ



Current-voltage characteristic at 300mK



10 μm

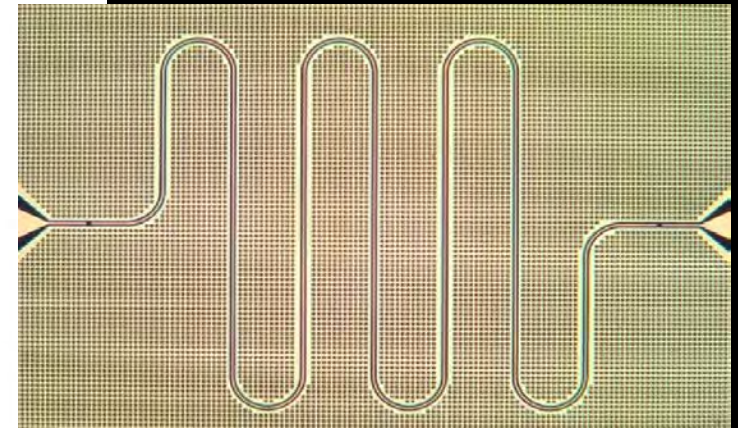
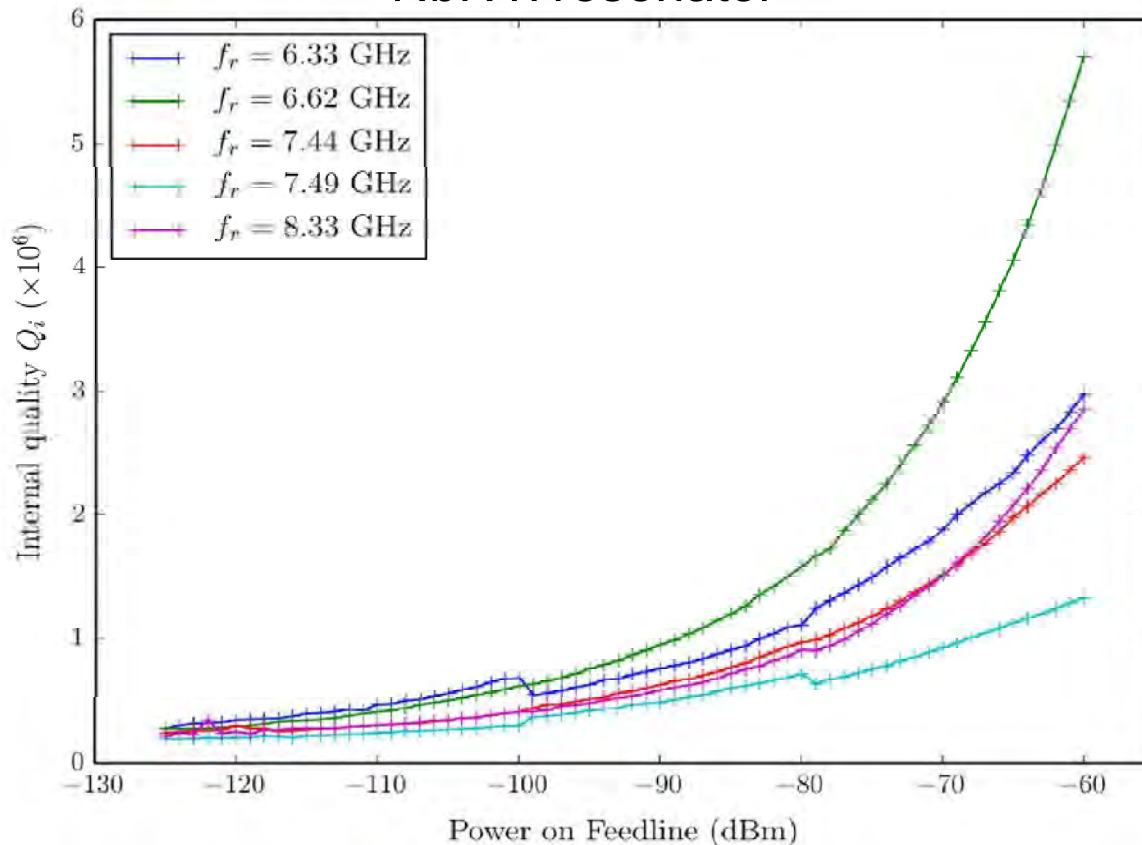


Cross JJ

Microwave resonators

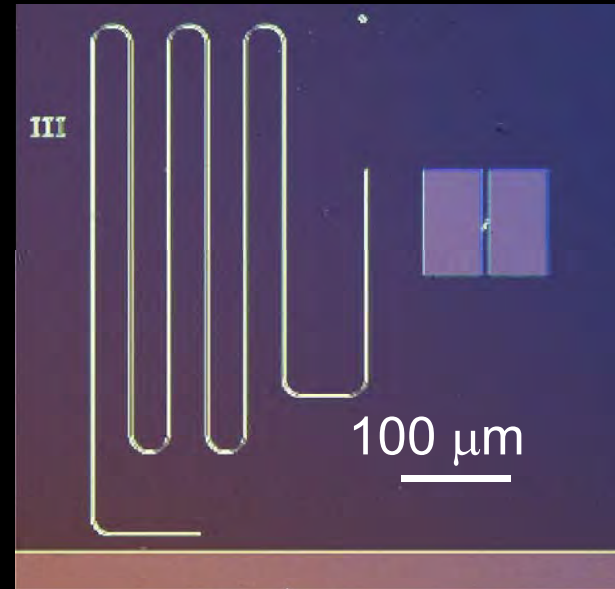
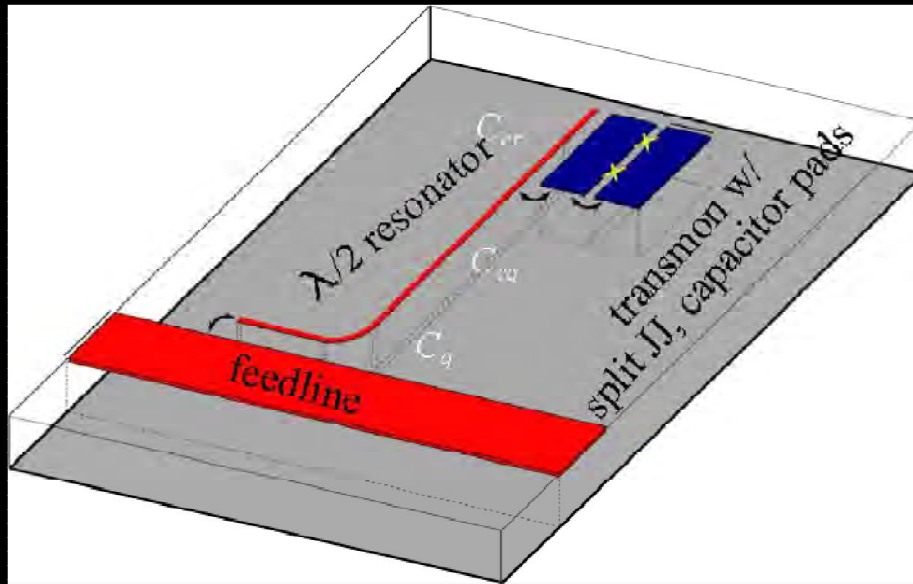
Internal quality factor versus power

NbN λ resonator

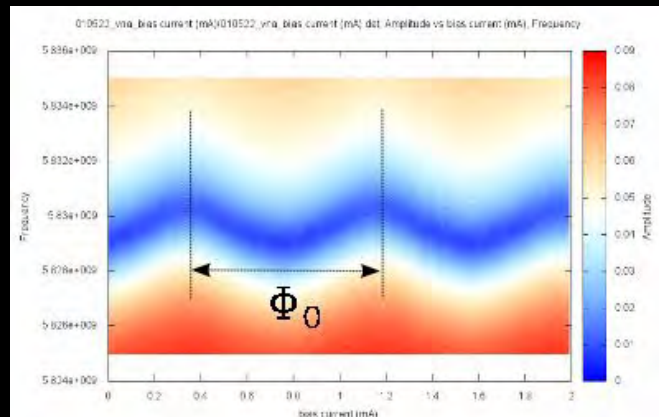


Al, Nb, NbN, and AlO_x resonators
quality factors Q : 100k @single photon, 1M+ @high power
Designs: Geometric, lumped element, spiral,
coplanar waveguide, microstrip

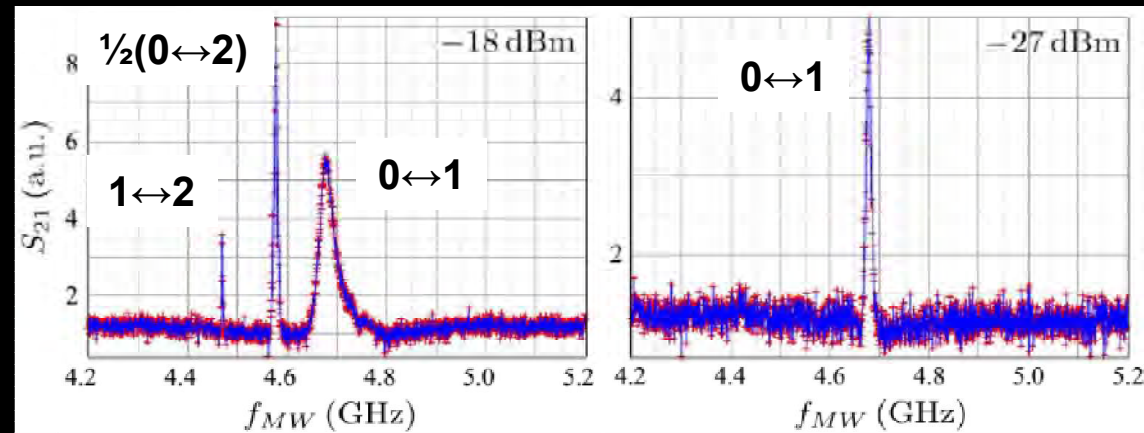
Microstrip transmon qubits (non-tunable and tunable)



Flux Φ to qubit
resonator response



Qubit spectroscopy
Increase drive power \rightarrow higher level visible



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Thanks for your attention